

### BCX52 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$P_{CM}$ : 0.5 W ( $T_{amb}=25^{\circ}C$ )

Collector current

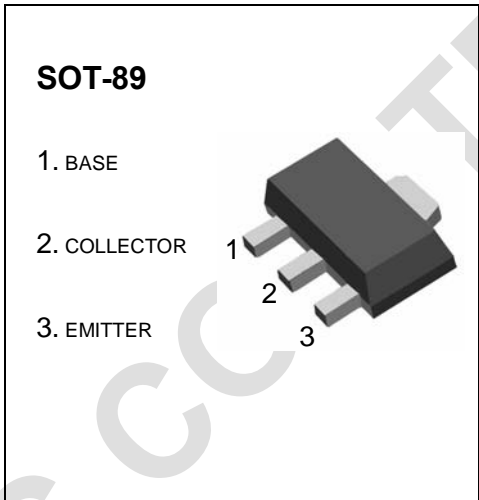
$I_{CM}$ : -1 A

Collector-base voltage

$V_{(BR)CBO}$ : -60 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-30V, I_E=0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$		-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-150mA$	63	250	
			63	160	
			100	250	
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-5mA$	63		
	$h_{FE(3)}$	$V_{CE}=-2V, I_C=-500mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$		-0.5	V
Base-emitter voltage	$V_{BE(ON)}$	$I_C=-500mA, V_{CE}=-2V$		-1	V
Transition frequency	$f_T$	$V_{CE}=-5V, I_C=-10mA$ $f = 100MHz$	50		MHz

<b>DEVICE MARKING</b>	BCX52=AE BCX52-10=AG BCX52-16=AM
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